High Conductance

1N482B thru 1N486B

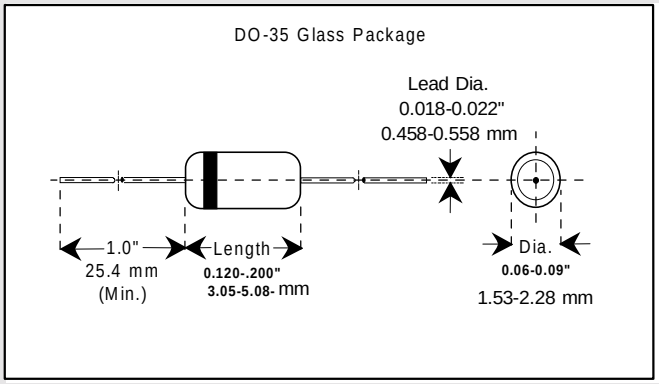
DO-35 Diodes

Use Advantages

Used as a general purpose diode in power supplies, or in clipping and steering applications. Operation at temperatures up to 200 degrees C, no derating. Can be used in harsh environments where hermeticity and low cost are important. Compatible with all major automatic pick and place mounting equipment. May be used on ceramic boards along with high temperature IR solder reflow.

Features

- Humidity proof glass
- Thermally matched system
- No thermal fatigue
- No applications restrictions
- Sigma Bond™ plated contacts
- 100% guaranteed solderability
- Problem free assembly
- Six Sigma quality
- LL-35 MiniMELF types available



Absolute Maximum Ratings	Symbol	Value	Unit
Average Forward Rectified Current at $T_{Ambient}$ = 25 °C	I_{AV}	0.65	Amp
Maximum Non-Repetitive Surge (8.3 mSecs. 1/2 sine)	I_{FSM}	2.0	Amps
Junction Temperature Range	T_j	-65 to +200	°C
Storage Temperature Range	T_S	-55 to +200	°C
Max. Average Power Dissipation	Pdiss	250	mW

Characteristics at T = 25°C

Type	Peak Inverse Voltage (MIN.) (PIV) Volts	Maximum Average Rectified Current (I_O) Amps	Maximum Forward Voltage Drop (V_F) @ 0.1A Volts	Maximum Leakage Current (I_R) @ PIV 25°C µA	150 °C µA	Minimum Saturation Voltage (@0.1 mA) Volts
1N482B	30	0.2	1.0	0.025	5	40
1N483B	60	0.2	1.0	0.025	5	80
1N484B	125	0.2	1.0	0.025	5	150
1N485B	175	0.2	1.0	0.025	5	200
1N486B	225	0.2	1.0	0.025	5	250

LL-35 Glass miniMELF package available, substitute an LL prefix instead of "1N"..

Microsemi

6 Lake Street - Lawrence, MA 01841

Tel: 978-681-0392 - Fax: 978-681-9135